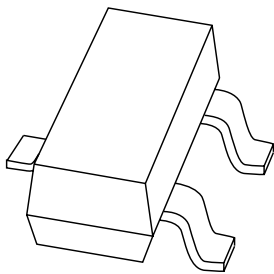


# DATA SHEET



**BF570**

NPN medium frequency transistor

Product data sheet  
Supersedes data of 2004 Jan 13

2004 Mar 15



## NPN medium frequency transistor

BF570

## FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 15 V)
- Low feedback capacitance (max. 2.2 pF).

## APPLICATIONS

- Monitors
- Battery equipped applications.

## DESCRIPTION

NPN transistor in a SOT23 plastic package.

## MARKING

| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| BF570       | 61* or B26                  |

## Note

1. \* = p : Made in Hong Kong.  
 \* = t : Made in Malaysia.  
 \* = W : Made in China.

## PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |

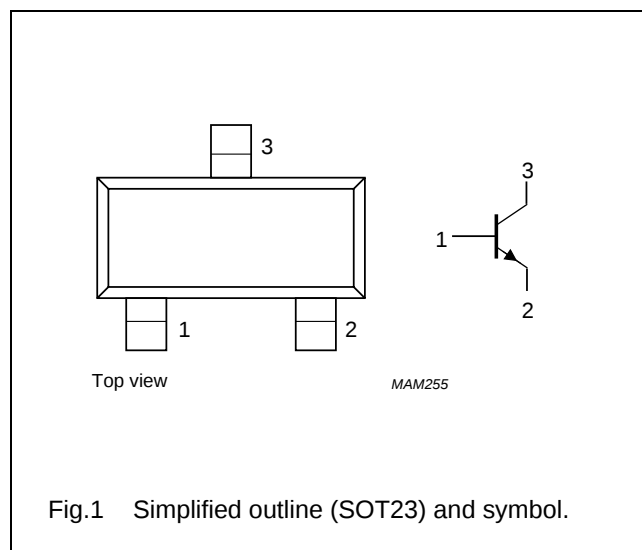


Fig.1 Simplified outline (SOT23) and symbol.

## ORDERING INFORMATION

| TYPE NUMBER | PACKAGE |                                          |         |
|-------------|---------|------------------------------------------|---------|
|             | NAME    | DESCRIPTION                              | VERSION |
| BF570       | –       | plastic surface mounted package; 3 leads | SOT23   |

## QUICK REFERENCE DATA

| SYMBOL    | PARAMETER                 | CONDITIONS                                                     | MIN. | MAX. | UNIT |
|-----------|---------------------------|----------------------------------------------------------------|------|------|------|
| $V_{CBO}$ | collector-base voltage    | open emitter                                                   | –    | 40   | V    |
| $V_{CEO}$ | collector-emitter voltage | open base                                                      | –    | 15   | V    |
| $I_{CM}$  | peak collector current    |                                                                | –    | 200  | mA   |
| $P_{tot}$ | total power dissipation   | $T_{amb} \leq 25\text{ °C}$                                    | –    | 250  | mW   |
| $h_{FE}$  | DC current gain           | $I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$                      | 40   | –    |      |
| $f_T$     | transition frequency      | $I_C = 40\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$ | 490  | –    | MHz  |

## NPN medium frequency transistor

BF570

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL    | PARAMETER                     | CONDITIONS                  | MIN. | MAX. | UNIT |
|-----------|-------------------------------|-----------------------------|------|------|------|
| $V_{CBO}$ | collector-base voltage        | open emitter                | –    | 40   | V    |
| $V_{CEO}$ | collector-emitter voltage     | open base                   | –    | 15   | V    |
| $V_{EBO}$ | emitter-base voltage          | open collector              | –    | 4.5  | V    |
| $I_C$     | collector current (DC)        |                             | –    | 100  | mA   |
| $I_{CM}$  | peak collector current        |                             | –    | 200  | mA   |
| $P_{tot}$ | total power dissipation       | $T_{amb} \leq 25\text{ °C}$ | –    | 250  | mW   |
| $T_{stg}$ | storage temperature           |                             | –65  | +150 | °C   |
| $T_j$     | junction temperature          |                             | –    | 150  | °C   |
| $T_{amb}$ | operating ambient temperature |                             | –65  | +150 | °C   |

## THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                                   | VALUE | UNIT |
|---------------|---------------------------------------------|-------|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | 500   | K/W  |

## CHARACTERISTICS

 $T_j = 25\text{ °C}$  unless otherwise specified.

| SYMBOL    | PARAMETER                 | CONDITIONS                                                     | MIN. | TYP. | MAX. | UNIT |
|-----------|---------------------------|----------------------------------------------------------------|------|------|------|------|
| $I_{CBO}$ | collector cut-off current | $I_E = 0\text{ A}; V_{CB} = 20\text{ V}$                       | –    | –    | 400  | nA   |
|           |                           | $I_E = 0\text{ A}; V_{CB} = 20\text{ V}; T_j = 125\text{ °C}$  | –    | –    | 30   | μA   |
| $I_{EBO}$ | emitter cut-off current   | $I_C = 0\text{ A}; V_{EB} = 2\text{ V}$                        | –    | –    | 100  | nA   |
| $h_{FE}$  | DC current gain           | $I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$                      | 40   | –    | –    |      |
| $C_{re}$  | feedback capacitance      | $I_C = 0\text{ A}; V_{CE} = 10\text{ V}; f = 1\text{ MHz}$     | –    | 1.6  | 2.2  | pF   |
| $f_T$     | transition frequency      | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$ | 500  | –    | –    | MHz  |
|           |                           | $I_C = 40\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$ | 490  | –    | –    | MHz  |

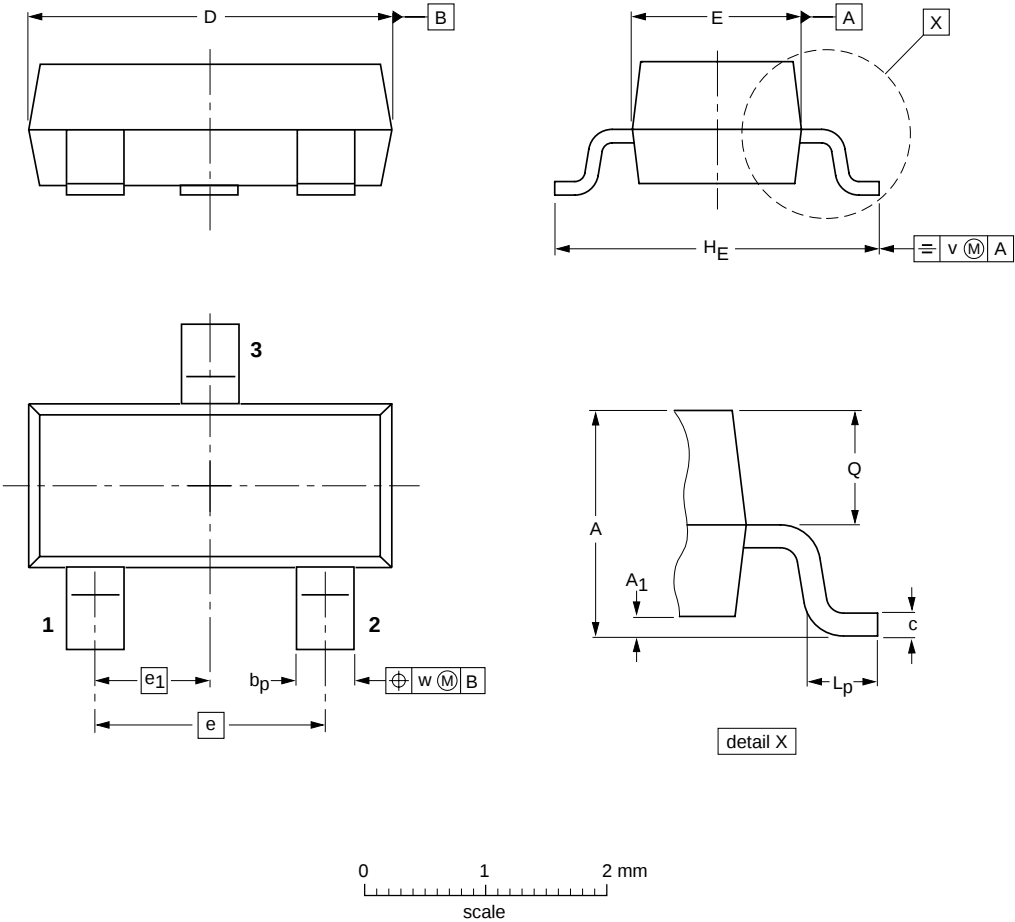
NPN medium frequency transistor

BF570

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | A <sub>1</sub><br>max. | b <sub>p</sub> | c            | D          | E          | e   | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | Q            | v   | w   |
|------|------------|------------------------|----------------|--------------|------------|------------|-----|----------------|----------------|----------------|--------------|-----|-----|
| mm   | 1.1<br>0.9 | 0.1                    | 0.48<br>0.38   | 0.15<br>0.09 | 3.0<br>2.8 | 1.4<br>1.2 | 1.9 | 0.95           | 2.5<br>2.1     | 0.45<br>0.15   | 0.55<br>0.45 | 0.2 | 0.1 |

| OUTLINE<br>VERSION | REFERENCES |          |       |  | EUROPEAN<br>PROJECTION                                                                | ISSUE DATE           |
|--------------------|------------|----------|-------|--|---------------------------------------------------------------------------------------|----------------------|
|                    | IEC        | JEDEC    | JEITA |  |                                                                                       |                      |
| SOT23              |            | TO-236AB |       |  |  | 04-11-04<br>06-03-16 |

## NPN medium frequency transistor

BF570

## DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION                                                                            |
|--------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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## **Customer notification**

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## **Contact information**

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